

Fig. 1

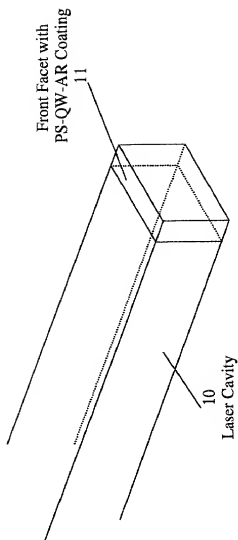


Fig. 2

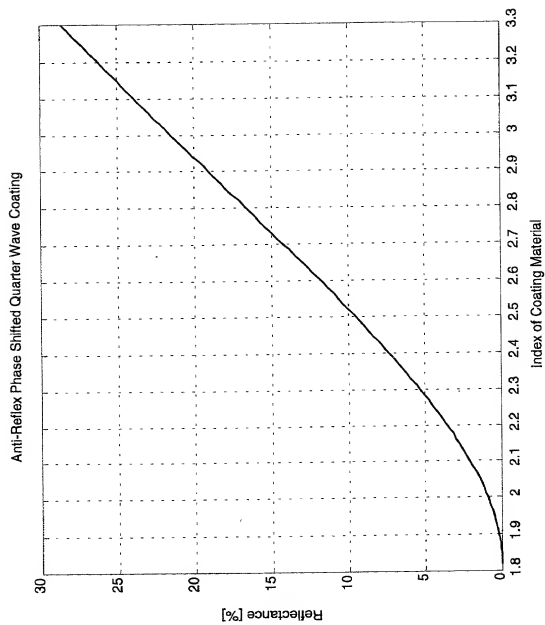
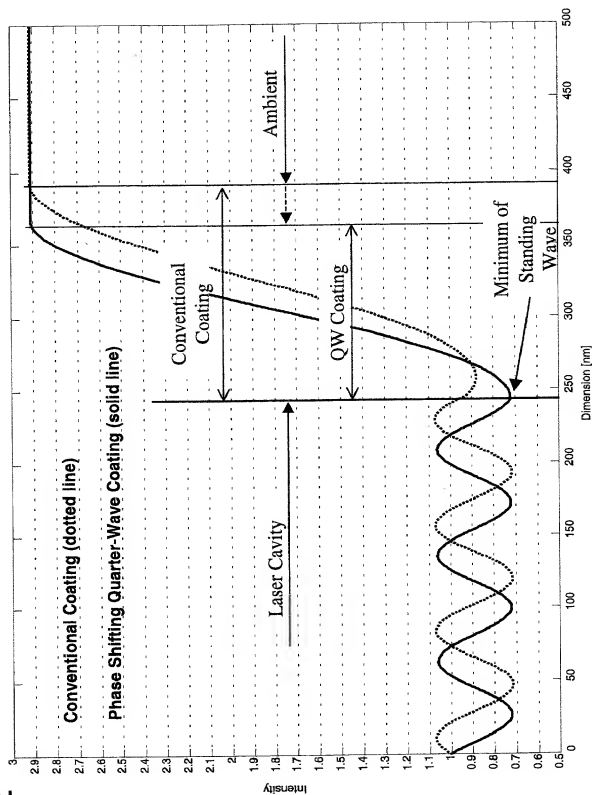


Fig. 3

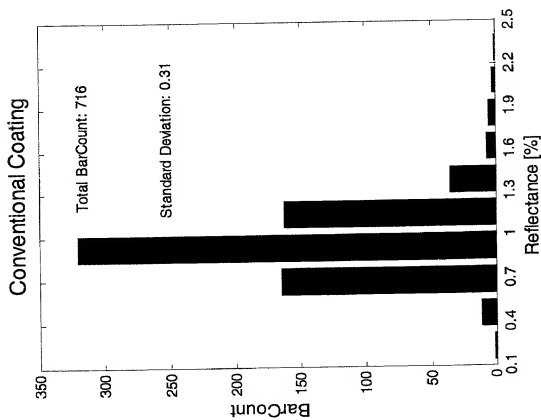
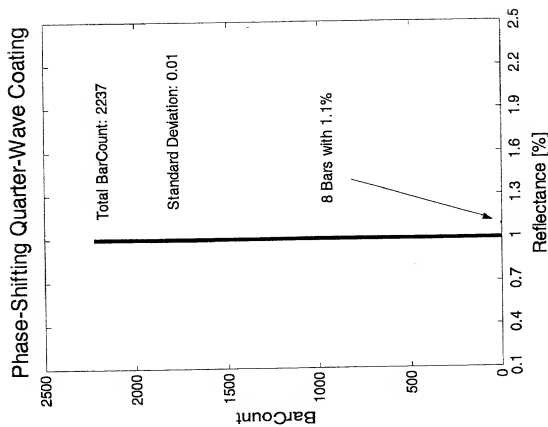
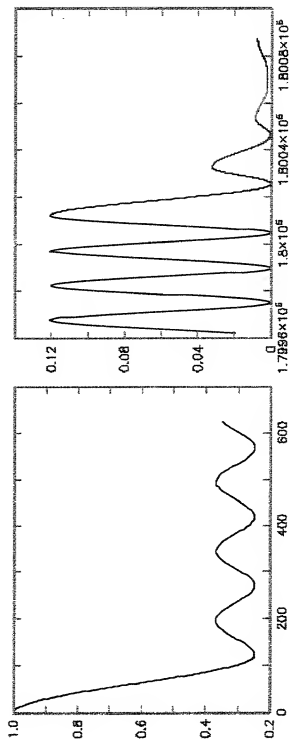
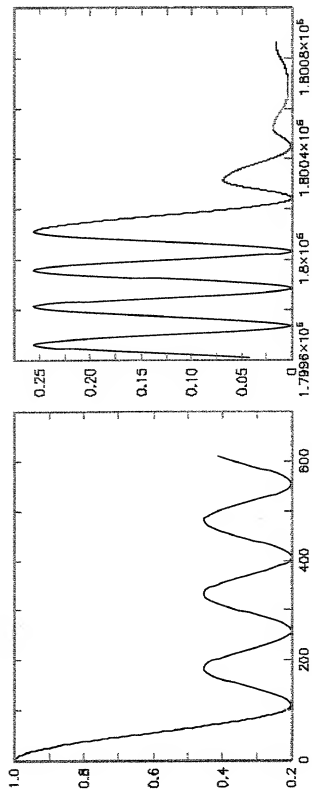
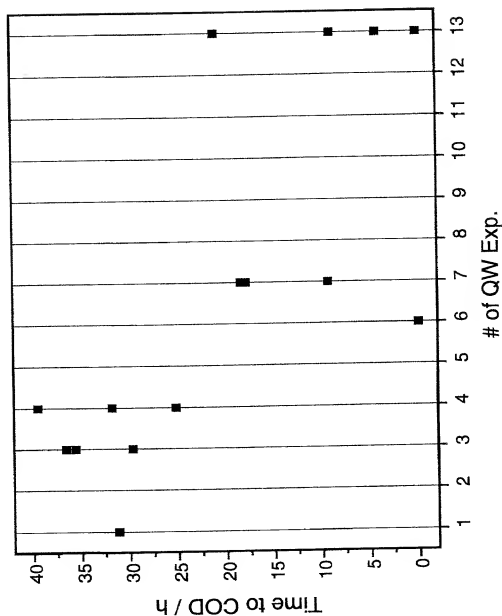
*Fig. 4(a)**Fig. 4 (b)*

Fig. 5

Phase Shifting Quarter Wave Coating with a 1 % Reflectance

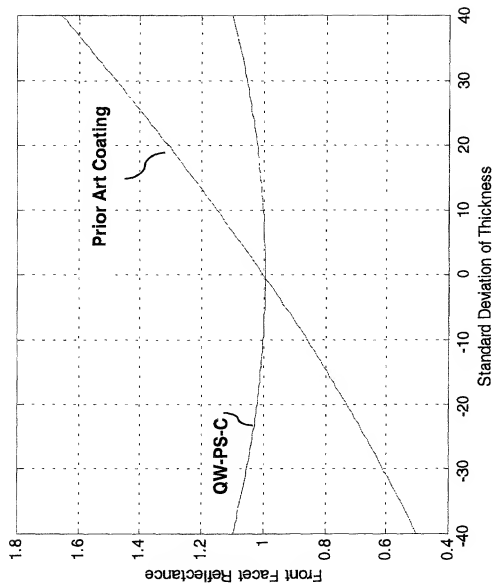
Fig. 6

Phase Shifting Quarter Wave Coating with a 4 % Reflectance

Fig. 7

Time to COD vs. # of QW Exp

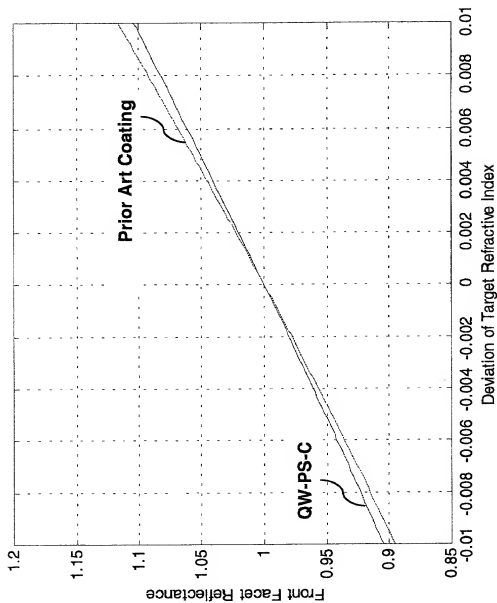
Fig. 8



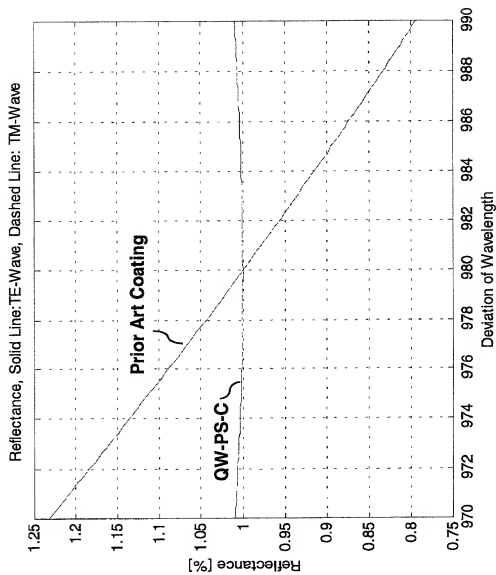
Dependence of reflectance on thickness variation



Fig. 9



Dependence of Reflectance on index variation

**Fig. 10**

Dependence of reflectance on wavelength variation

Fig. 11

## Process parameters

Coating	2%SiH4/He	N2	NH3	Plasma Power	Substrate Temp	Pressure
Prior art	300 sccm	330 sccm	Variable (~11.5sccm)	20 Watts	300 °C	1.4 Torr
QW-PS-C	403 sccm	35 sccm	Variable (~12.2sccm)	25 Watts	300 °C	1.4 Torr